

GaAlAs Infrared Emitter

OPE5794

The **OPE5794** is GaAlAs infrared emitting diode that is designed for high radiant intensity and low forward voltage. This device is optimized for efficiency at emission wavelength 940nm and has a high radiant efficiency over a wide range of forward current. This device is packaged T1 plastic package and has medium beam angle with lensed package and cup frame

FEATURES

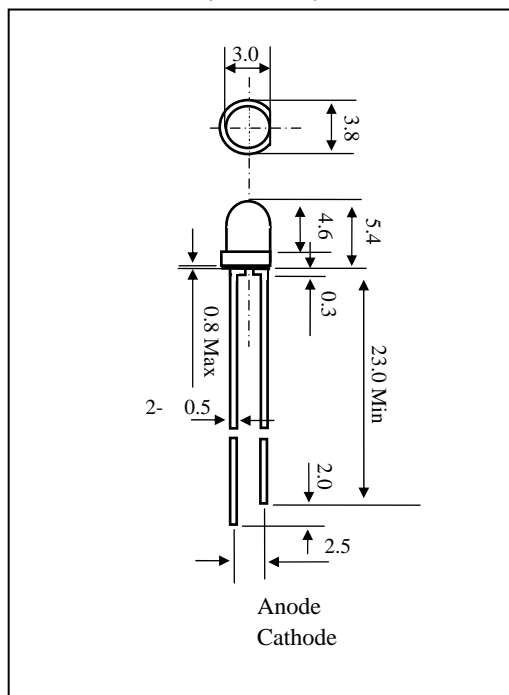
- High-output power
- Medium beam angle
- Available for pulse operating

APPLICATIONS

- Optical emitters
- Optical switches
- Smoke sensors
- IR remote control
- IR sound transmission

* Please take proper steps in order to secure reliability and safety in required conditions and environments for this device.

DIMENSIONS (Unit:mm)



MAXIMUM RATINGS

(Ta=25°C)

Item	Symbol	Rating	Unit
Power dissipation	P _D	80	mW
Forward current	I _F	60	mA
Pulse forward current	I _{FP}	0.8	A
Reverse voltage	V _R	5.0	V
Operating temp.	T _{opr.}	-20~ +70	°C
Storage temp.	T _{stg.}	-20~ +80	°C
Soldering temp.	T _{sol.}	240.	°C

¹.Duty ratio = 1/100, pulse width=0.12ms.

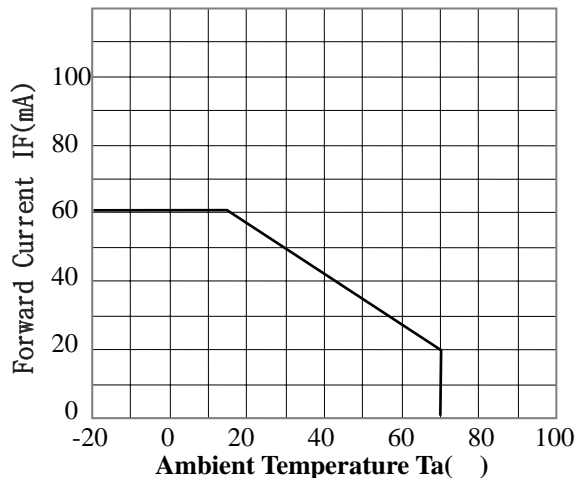
².Lead Soldering Temperature (2mm from case for 5sec.).

ELECTRO-OPTICAL CHARACTERISTICS

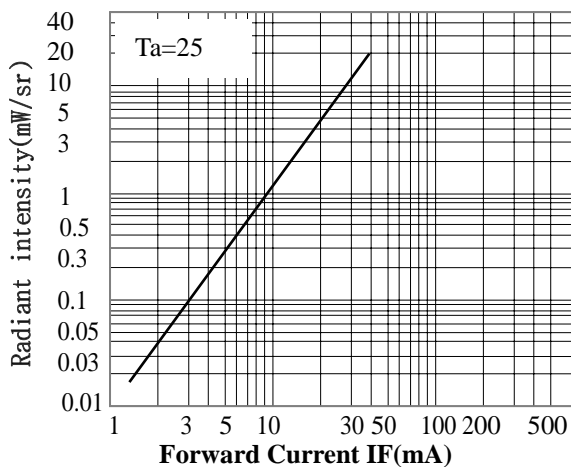
(Ta=25°C)

Item	Symbol	Conditions	Min.	Typ.	Max.	Unit
Forward voltage	V _F	I _F =40mA		1.2	1.5	V
Reverse current	I _R	V _R = 5V			10	μA
Capacitance	C _t	f = 1MHz		20		pF
Radiant intensity	I _e	I _F =40mA		20		mW/sr
Peak emission wavelength	λ _p	I _F = 40mA		940		nm
Spectral bandwidth 50%		I _F = 40mA		45		nm
Half angle		I _F =40mA		±17		deg.

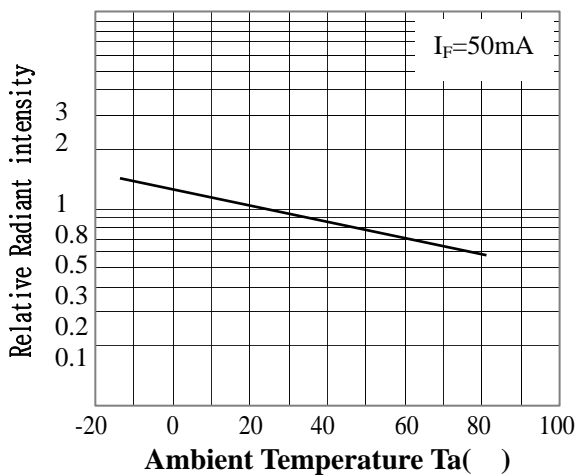
- **FORWARD CURRENT Vs. AMBIENT TEMP.**



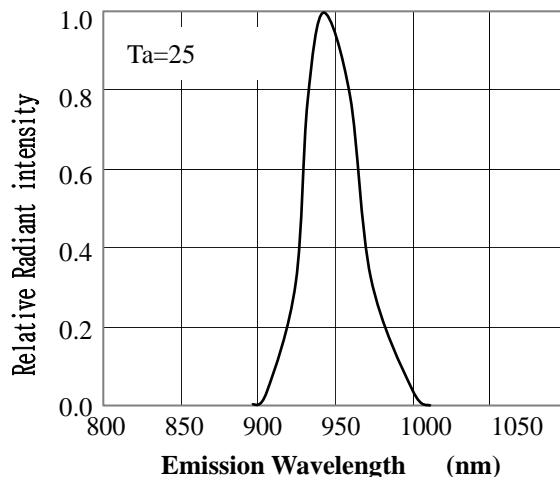
- **RADIANT INTENSITY Vs. FORWARD CURRENT.**



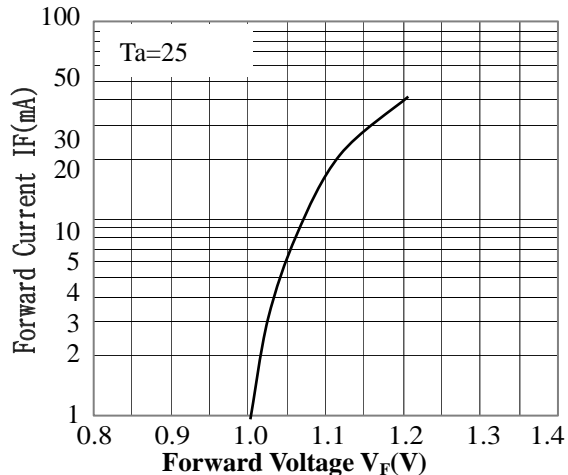
- **RELATIVE RADIANT INTENSITY Vs. AMBIENT TEMP.**



- **RELATIVE RADIANT INTENSITY Vs. EMISSION WAVELENGTH.**



- **FORWARD CURRENT Vs. FORWARD VOLTAGE**



- **ANGULAR DISPLACEMENT Vs. RELATIVE RADIANT INTENSITY**

